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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	400
Number of Logic Elements/Cells	4000
Total RAM Bits	78336
Number of I/O	249
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	324-BGA
Supplier Device Package	324-FBGA (19x19)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/intel/ep1c4f324c6">https://www.e-xfl.com/product-detail/intel/ep1c4f324c6</a>

to the appropriate plane on the board. The Quartus II software reserves I/O pins as power pins as necessary for layout with the larger densities in the same package having more power pins.

**Table 1–3. Cyclone QFP and FineLine BGA Package Sizes**

Dimension	100-Pin TQFP	144-Pin TQFP	240-Pin PQFP	256-Pin FineLine BGA	324-Pin FineLine BGA	400-Pin FineLine BGA
Pitch (mm)	0.5	0.5	0.5	1.0	1.0	1.0
Area (mm <sup>2</sup> )	256	484	1,024	289	361	441
Length × width (mm × mm)	16×16	22×22	34.6×34.6	17×17	19×19	21×21

## Document Revision History

Table 1–4 shows the revision history for this document.

**Table 1–4. Document Revision History**

Date and Document Version	Changes Made	Summary of Changes
May 2008 v1.5	Minor textual and style changes.	—
January 2007 v1.4	Added document revision history.	—
August 2005 v1.3	Minor updates.	—
October 2003 v1.2	Added 64-bit PCI support information.	—
September 2003 v1.1	<ul style="list-style-type: none"> <li>Updated LVDS data rates to 640 Mbps from 311 Mbps.</li> <li>Updated RSDS feature information.</li> </ul>	—
May 2003 v1.0	Added document to Cyclone Device Handbook.	—



functions. Another special packing mode allows the register output to feed back into the LUT of the same LE so that the register is packed with its own fan-out LUT. This provides another mechanism for improved fitting. The LE can also drive out registered and unregistered versions of the LUT output.

## LUT Chain and Register Chain

In addition to the three general routing outputs, the LEs within a LAB have LUT chain and register chain outputs. LUT chain connections allow LUTs within the same LAB to cascade together for wide input functions. Register chain outputs allow registers within the same LAB to cascade together. The register chain output allows a LAB to use LUTs for a single combinatorial function and the registers to be used for an unrelated shift register implementation. These resources speed up connections between LABs while saving local interconnect resources. [“MultiTrack Interconnect” on page 2–12](#) for more information on LUT chain and register chain connections.

## addnsub Signal

The LE's dynamic adder/subtractor feature saves logic resources by using one set of LEs to implement both an adder and a subtractor. This feature is controlled by the LAB-wide control signal `addnsub`. The `addnsub` signal sets the LAB to perform either  $A + B$  or  $A - B$ . The LUT computes addition; subtraction is computed by adding the two's complement of the intended subtractor. The LAB-wide signal converts to two's complement by inverting the B bits within the LAB and setting carry-in = 1 to add one to the least significant bit (LSB). The LSB of an adder/subtractor must be placed in the first LE of the LAB, where the LAB-wide `addnsub` signal automatically sets the carry-in to 1. The Quartus II Compiler automatically places and uses the adder/subtractor feature when using adder/subtractor parameterized functions.

## LE Operating Modes

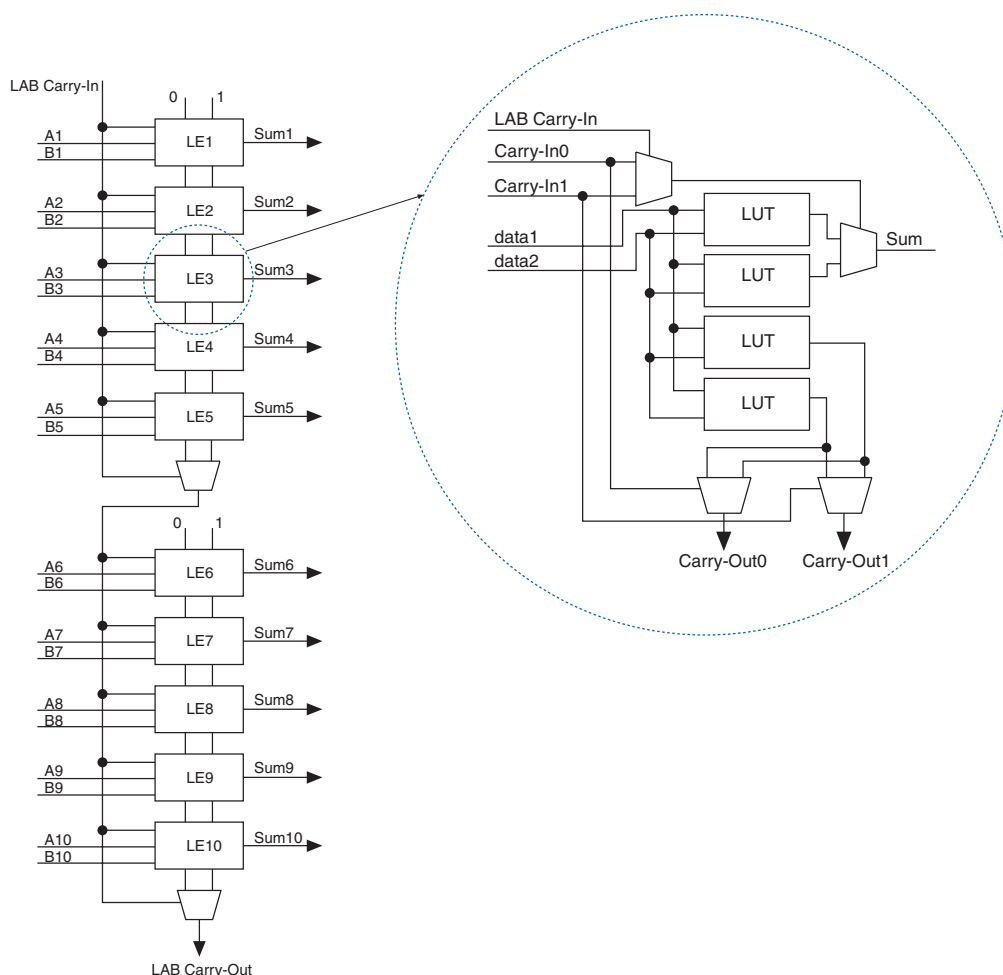
The Cyclone LE can operate in one of the following modes:

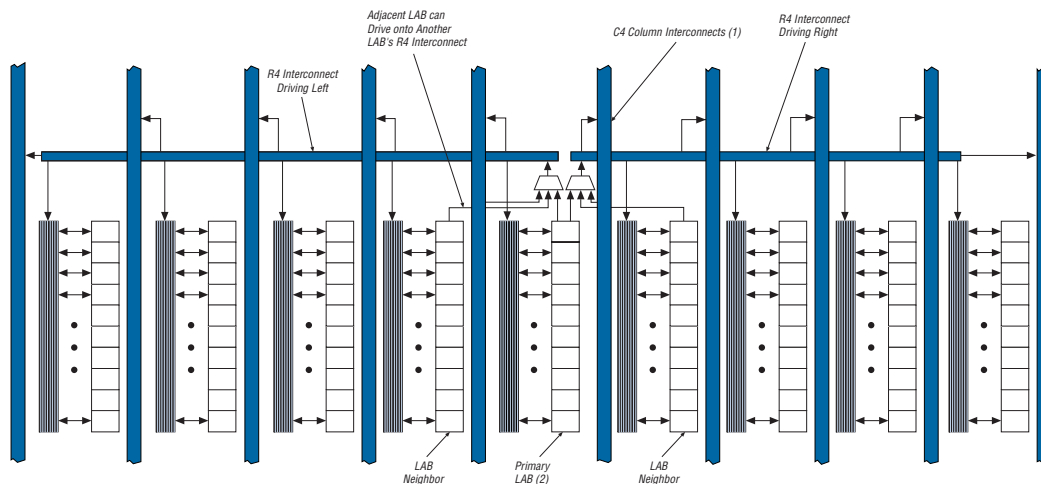
- Normal mode
- Dynamic arithmetic mode

Each mode uses LE resources differently. In each mode, eight available inputs to the LE—the four data inputs from the LAB local interconnect, `carry-in0` and `carry-in1` from the previous LE, the LAB carry-in from the previous carry-chain LAB, and the register chain connection—are directed to different destinations to implement the desired logic function. LAB-wide signals provide clock, asynchronous clear, asynchronous

Figure 2–8 shows the carry-select circuitry in a LAB for a 10-bit full adder. One portion of the LUT generates the sum of two bits using the input signals and the appropriate carry-in bit; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT generates carry-out bits. A LAB-wide carry-in bit selects which chain is used for the addition of given inputs. The carry-in signal for each chain, *carry-in0* or *carry-in1*, selects the carry-out to carry forward to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is fed to local, row, or column interconnects.

**Figure 2–8. Carry Select Chain**



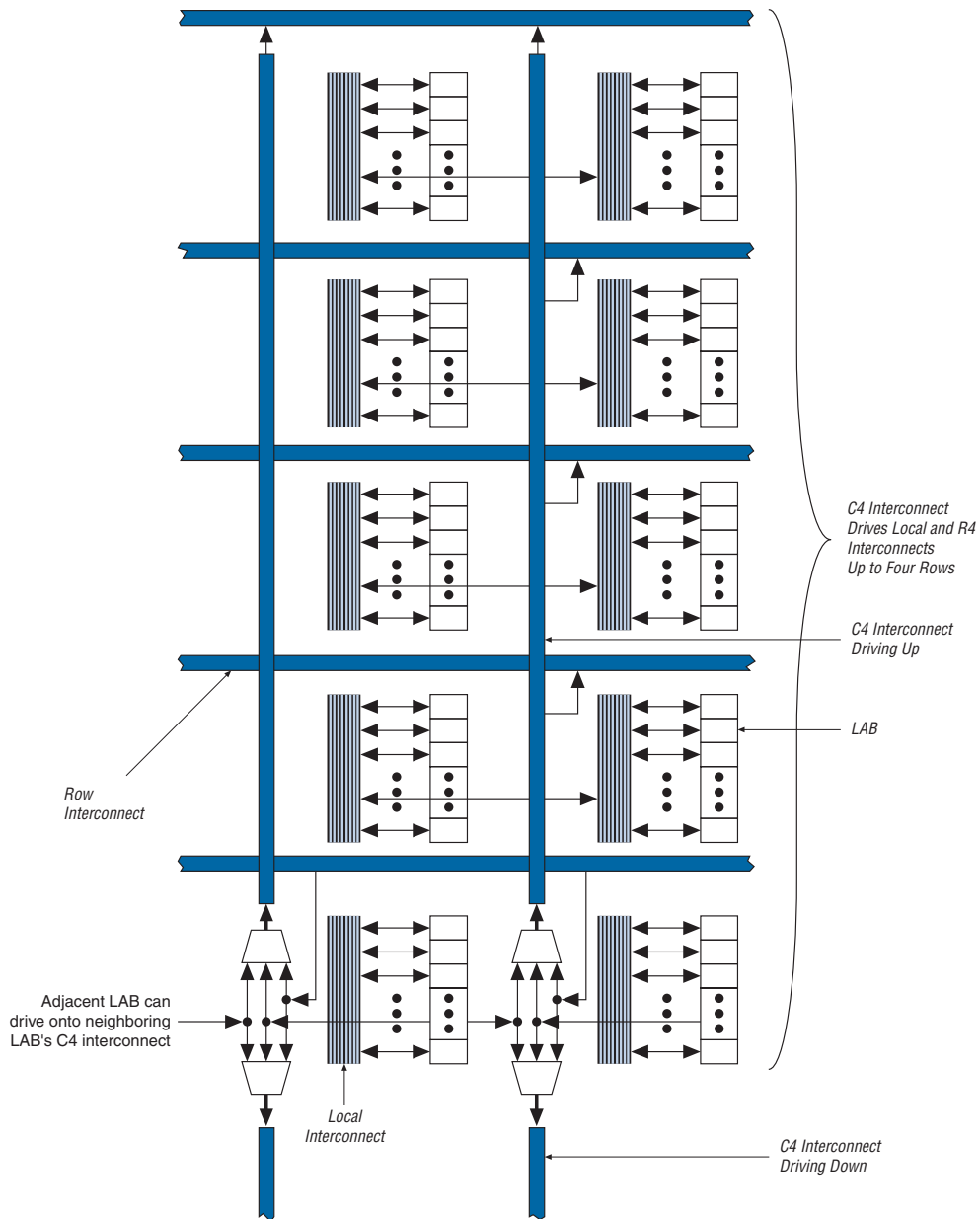
**Figure 2–9. R4 Interconnect Connections****Notes to Figure 2–9:**

- (1) C4 interconnects can drive R4 interconnects.
- (2) This pattern is repeated for every LAB in the LAB row.

The column interconnect operates similarly to the row interconnect. Each column of LABs is served by a dedicated column interconnect, which vertically routes signals to and from LABs, M4K memory blocks, and row and column IOEs. These column resources include:

- LUT chain interconnects within a LAB
- Register chain interconnects within a LAB
- C4 interconnects traversing a distance of four blocks in an up and down direction

Cyclone devices include an enhanced interconnect structure within LABs for routing LE output to LE input connections faster using LUT chain connections and register chain connections. The LUT chain connection allows the combinatorial output of an LE to directly drive the fast input of the LE right below it, bypassing the local interconnect. These resources can be used as a high-speed connection for wide fan-in functions from LE 1 to LE 10 in the same LAB. The register chain connection allows the register output of one LE to connect directly to the register input of the next LE in the LAB for fast shift registers. The Quartus II Compiler automatically takes advantage of these resources to improve utilization and performance. Figure 2–10 shows the LUT chain and register chain interconnects.

**Figure 2–11. C4 Interconnect Connections** *Note (1)***Note to Figure 2–11:**

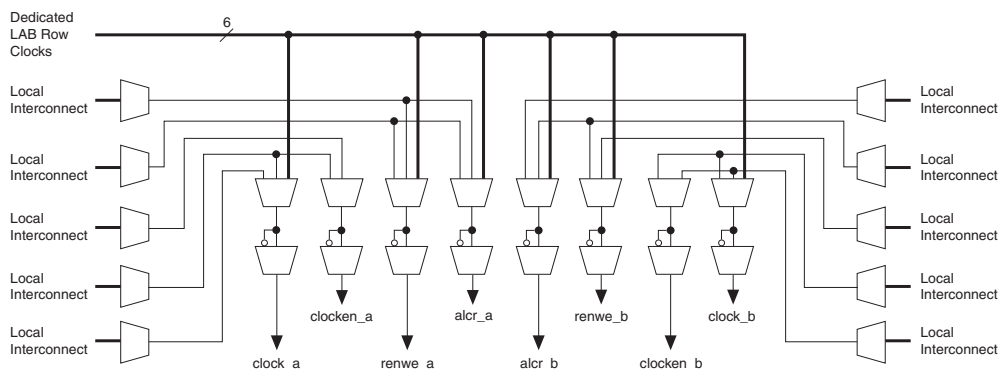
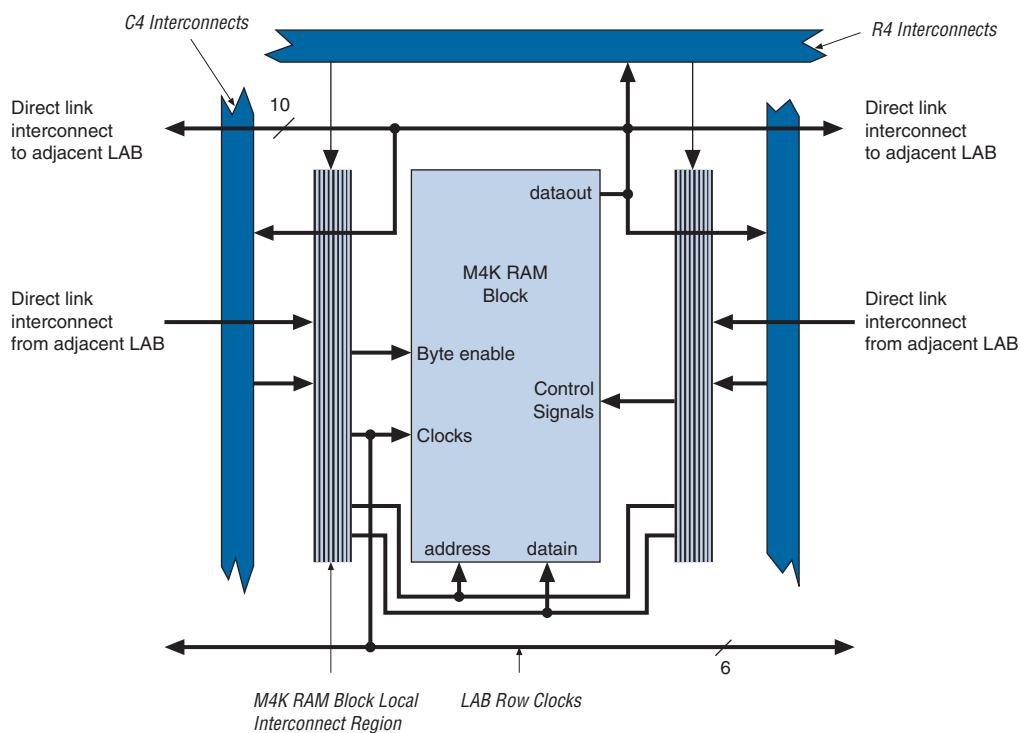
(1) Each C4 interconnect can drive either up or down four rows.

All embedded blocks communicate with the logic array similar to LAB-to-LAB interfaces. Each block (i.e., M4K memory or PLL) connects to row and column interconnects and has local interconnect regions driven by row and column interconnects. These blocks also have direct link interconnects for fast connections to and from a neighboring LAB.

Table 2–2 shows the Cyclone device's routing scheme.

<b>Table 2–2. Cyclone Device Routing Scheme</b>											
<b>Source</b>	<b>Destination</b>										
	<b>LUT Chain</b>	<b>Register Chain</b>	<b>Local Interconnect</b>	<b>Direct Link Interconnect</b>	<b>R4 Interconnect</b>	<b>C4 Interconnect</b>	<b>LE</b>	<b>M4K RAM Block</b>	<b>PLL</b>	<b>Column IOE</b>	<b>Row IOE</b>
LUT Chain	—	—	—	—	—	—	✓	—	—	—	—
Register Chain	—	—	—	—	—	—	✓	—	—	—	—
Local Interconnect	—	—	—	—	—	—	✓	✓	✓	✓	✓
Direct Link Interconnect	—	—	✓	—	—	—	—	—	—	—	—
R4 Interconnect	—	—	✓	—	✓	✓	—	—	—	—	—
C4 Interconnect	—	—	✓	—	✓	✓	—	—	—	—	—
LE	✓	✓	✓	✓	✓	✓	—	—	—	—	—
M4K RAM Block	—	—	✓	✓	✓	✓	—	—	—	—	—
PLL	—	—	—	✓	✓	✓	—	—	—	—	—
Column IOE	—	—	—	—	—	✓	—	—	—	—	—
Row IOE	—	—	—	✓	✓	✓	—	—	—	—	—



**Figure 2–15. M4K RAM Block Control Signals****Figure 2–16. M4K RAM Block LAB Row Interface**

Notes (1), (2)



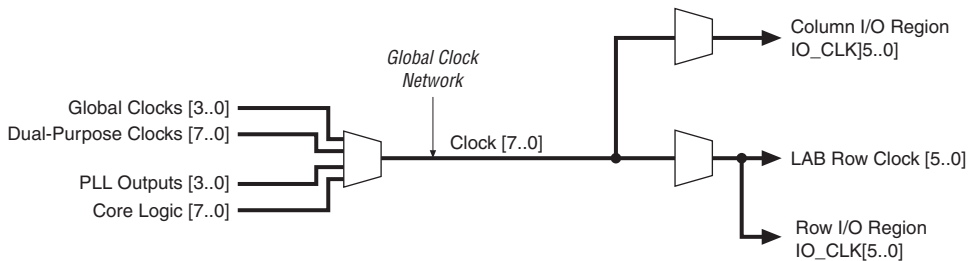
## Dual-Purpose Clock Pins

Each Cyclone device except the EP1C3 device has eight dual-purpose clock pins,  $DPCLK[7..0]$  (two on each I/O bank). EP1C3 devices have five  $DPCLK$  pins in the 100-pin TQFP package. These dual-purpose pins can connect to the global clock network (see [Figure 2–22](#)) for high-fanout control signals such as clocks, asynchronous clears, presets, and clock enables, or protocol control signals such as  $TRDY$  and  $IRDY$  for PCI, or  $DQS$  signals for external memory interfaces.

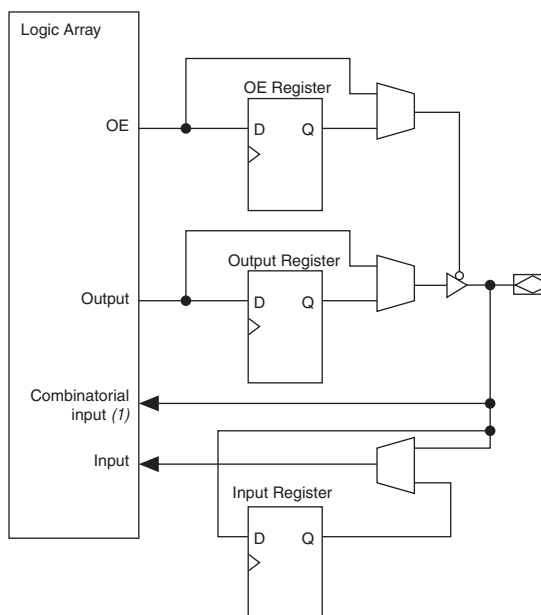
## Combined Resources

Each Cyclone device contains eight distinct dedicated clocking resources. The device uses multiplexers with these clocks to form six-bit buses to drive LAB row clocks, column IOE clocks, or row IOE clocks. See [Figure 2–23](#). Another multiplexer at the LAB level selects two of the six LAB row clocks to feed the LE registers within the LAB.

**Figure 2–23. Global Clock Network Multiplexers**



IOE clocks have row and column block regions. Six of the eight global clock resources feed to these row and column regions. [Figure 2–24](#) shows the I/O clock regions.

**Figure 2–27. Cyclone IOE Structure****Note to Figure 2–27:**

- (1) There are two paths available for combinatorial inputs to the logic array. Each path contains a unique programmable delay chain.

The IOEs are located in I/O blocks around the periphery of the Cyclone device. There are up to three IOEs per row I/O block and up to three IOEs per column I/O block (column I/O blocks span two columns). The row I/O blocks drive row, column, or direct link interconnects. The column I/O blocks drive column interconnects. Figure 2–28 shows how a row I/O block connects to the logic array. Figure 2–29 shows how a column I/O block connects to the logic array.

<b>Table 2–10. DQ Pin Groups (Part 2 of 2)</b>			
<b>Device</b>	<b>Package</b>	<b>Number of × 8 DQ Pin Groups</b>	<b>Total DQ Pin Count</b>
EP1C6	144-pin TQFP	4	32
	240-pin PQFP	4	32
	256-pin FineLine BGA	4	32
EP1C12	240-pin PQFP	4	32
	256-pin FineLine BGA	4	32
	324-pin FineLine BGA	8	64
EP1C20	324-pin FineLine BGA	8	64
	400-pin FineLine BGA	8	64

**Note to Table 2–10:**

- (1) EP1C3 devices in the 100-pin TQFP package do not have any DQ pin groups in I/O bank 1.

A programmable delay chain on each DQS pin allows for either a 90° phase shift (for DDR SDRAM), or a 72° phase shift (for FCRAM) which automatically center-aligns input DQS synchronization signals within the data window of their corresponding DQ data signals. The phase-shifted DQS signals drive the global clock network. This global DQS signal clocks DQ signals on internal LE registers.

These DQS delay elements combine with the PLL's clocking and phase shift ability to provide a complete hardware solution for interfacing to high-speed memory.

The clock phase shift allows the PLL to clock the DQ output enable and output paths. The designer should use the following guidelines to meet 133 MHz performance for DDR SDRAM and FCRAM interfaces:

- The DQS signal must be in the middle of the DQ group it clocks
- Resynchronize the incoming data to the logic array clock using successive LE registers or FIFO buffers
- LE registers must be placed in the LAB adjacent to the DQ I/O pin column it is fed by

Figure 2–34 illustrates DDR SDRAM and FCRAM interfacing from the I/O through the dedicated circuitry to the logic array.

Each I/O bank can support multiple standards with the same  $V_{CCIO}$  for input and output pins. For example, when  $V_{CCIO}$  is 3.3-V, a bank can support LVTTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

## LVDS I/O Pins

A subset of pins in all four I/O banks supports LVDS interfacing. These dual-purpose LVDS pins require an external-resistor network at the transmitter channels in addition to 100- $\Omega$  termination resistors on receiver channels. These pins do not contain dedicated serialization or deserialization circuitry; therefore, internal logic performs serialization and deserialization functions.

Table 2–13 shows the total number of supported LVDS channels per device density.

<b>Table 2–13. Cyclone Device LVDS Channels</b>		
<b>Device</b>	<b>Pin Count</b>	<b>Number of LVDS Channels</b>
EP1C3	100	(1)
	144	34
EP1C4	324	103
	400	129
EP1C6	144	29
	240	72
	256	72
EP1C12	240	66
	256	72
	324	103
EP1C20	324	95
	400	129

**Note to Table 2–13:**

- (1) EP1C3 devices in the 100-pin TQFP package do not support the LVDS I/O standard.

## MultiVolt I/O Interface

The Cyclone architecture supports the MultiVolt I/O interface feature, which allows Cyclone devices in all packages to interface with systems of different supply voltages. The devices have one set of  $V_{CC}$  pins for internal operation and input buffers ( $V_{CCINT}$ ), and four sets for I/O output drivers ( $V_{CCIO}$ ).

The Cyclone  $V_{CCINT}$  pins must always be connected to a 1.5-V power supply. If the  $V_{CCINT}$  level is 1.5 V, then input pins are 1.5-V, 1.8-V, 2.5-V, and 3.3-V tolerant. The  $V_{CCIO}$  pins can be connected to either a 1.5-V, 1.8-V, 2.5-V, or 3.3-V power supply, depending on the output requirements. The output levels are compatible with systems of the same voltage as the power supply (i.e., when  $V_{CCIO}$  pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When  $V_{CCIO}$  pins are connected to a 3.3-V power supply, the output high is 3.3-V and is compatible with 3.3-V or 5.0-V systems. Table 2–14 summarizes Cyclone MultiVolt I/O support.

**Table 2–14. Cyclone MultiVolt I/O Support** *Note (1)*

$V_{CCIO}$ (V)	Input Signal					Output Signal				
	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	✓	✓	✓ (2)	✓ (2)	—	✓	—	—	—	—
1.8	✓	✓	✓ (2)	✓ (2)	—	✓ (3)	✓	—	—	—
2.5	—	—	✓	✓	—	✓ (5)	✓ (5)	✓	—	—
3.3	—	—	✓ (4)	✓	✓ (6)	✓ (7)	✓ (7)	✓ (7)	✓	✓ (8)

**Notes to Table 2–14:**

- (1) The PCI clamping diode must be disabled to drive an input with voltages higher than  $V_{CCIO}$ .
- (2) When  $V_{CCIO}$  = 1.5-V or 1.8-V and a 2.5-V or 3.3-V input signal feeds an input pin, higher pin leakage current is expected. Turn on **Allow voltage overdrive for LVTTL / LVCMOS input pins** in the Assignments > Device > Device and Pin Options > Pin Placement tab when a device has this I/O combinations.
- (3) When  $V_{CCIO}$  = 1.8-V, a Cyclone device can drive a 1.5-V device with 1.8-V tolerant inputs.
- (4) When  $V_{CCIO}$  = 3.3-V and a 2.5-V input signal feeds an input pin, the  $V_{CCIO}$  supply current will be slightly larger than expected.
- (5) When  $V_{CCIO}$  = 2.5-V, a Cyclone device can drive a 1.5-V or 1.8-V device with 2.5-V tolerant inputs.
- (6) Cyclone devices can be 5.0-V tolerant with the use of an external resistor and the internal PCI clamp diode.
- (7) When  $V_{CCIO}$  = 3.3-V, a Cyclone device can drive a 1.5-V, 1.8-V, or 2.5-V device with 3.3-V tolerant inputs.
- (8) When  $V_{CCIO}$  = 3.3-V, a Cyclone device can drive a device with 5.0-V LVTTL inputs but not 5.0-V LVCMOS inputs.

## Power Sequencing and Hot Socketing

Because Cyclone devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the  $V_{CCIO}$  and  $V_{CCINT}$  power supplies may be powered in any order.

Signals can be driven into Cyclone devices before and during power up without damaging the device. In addition, Cyclone devices do not drive out during power up. Once operating conditions are reached and the device is configured, Cyclone devices operate as specified by the user.

## Operating Modes

The Cyclone architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. Together, the configuration and initialization processes are called command mode. Normal device operation is called user mode.

SRAM configuration elements allow Cyclone devices to be reconfigured in-circuit by loading new configuration data into the device. With real-time reconfiguration, the device is forced into command mode with a device pin. The configuration process loads different configuration data, reinitializes the device, and resumes user-mode operation. Designers can perform in-field upgrades by distributing new configuration files either within the system or remotely.

A built-in weak pull-up resistor pulls all user I/O pins to  $V_{CCIO}$  before and during device configuration.

The configuration pins support 1.5-V/1.8-V or 2.5-V/3.3-V I/O standards. The voltage level of the configuration output pins is determined by the  $V_{CCIO}$  of the bank where the pins reside. The bank  $V_{CCIO}$  selects whether the configuration inputs are 1.5-V, 1.8-V, 2.5-V, or 3.3-V compatible.

## Configuration Schemes

Designers can load the configuration data for a Cyclone device with one of three configuration schemes (see [Table 3–5](#)), chosen on the basis of the target application. Designers can use a configuration device, intelligent controller, or the JTAG port to configure a Cyclone device. A low-cost configuration device can automatically configure a Cyclone device at system power-up.



Typically, the user-mode current during device operation is lower than the power-up current in Table 4–17. Altera recommends using the Cyclone Power Calculator, available on the Altera web site, to estimate the user-mode  $I_{CCINT}$  consumption and then select power supplies or regulators based on the higher value.

## Timing Model

The DirectDrive technology and MultiTrack interconnect ensure predictable performance, accurate simulation, and accurate timing analysis across all Cyclone device densities and speed grades. This section describes and specifies the performance, internal, external, and PLL timing specifications.

All specifications are representative of worst-case supply voltage and junction temperature conditions.

### Preliminary and Final Timing

Timing models can have either preliminary or final status. The Quartus® II software issues an informational message during the design compilation if the timing models are preliminary. Table 4–18 shows the status of the Cyclone device timing models.

Preliminary status means the timing model is subject to change. Initially, timing numbers are created using simulation results, process data, and other known parameters. These tests are used to make the preliminary numbers as close to the actual timing parameters as possible.

Final timing numbers are based on actual device operation and testing. These numbers reflect the actual performance of the device under worst-case voltage and junction temperature conditions.

**Table 4–18. Cyclone Device Timing Model Status**

Device	Preliminary	Final
EP1C3	—	✓
EP1C4	—	✓
EP1C6	—	✓
EP1C12	—	✓
EP1C20	—	✓

**Table 4–20. Cyclone Device Performance**

Resource Used	Design Size and Function	Mode	Resources Used			Performance		
			LEs	M4K Memory Bits	M4K Memory Blocks	-6 Speed Grade (MHz)	-7 Speed Grade (MHz)	-8 Speed Grade (MHz)
M4K memory block	RAM 128 × 36 bit	Single port	—	4,608	1	256.00	222.67	197.01
	RAM 128 × 36 bit	Simple dual-port mode	—	4,608	1	255.95	222.67	196.97
	RAM 256 × 18 bit	True dual-port mode	—	4,608	1	255.95	222.67	196.97
	FIFO 128 × 36 bit	—	40	4,608	1	256.02	222.67	197.01
	Shift register 9 × 4 × 128	Shift register	11	4,536	1	255.95	222.67	196.97

*Note to Table 4–20:*

(1) The performance numbers for this function are from an EP1C6 device in a 240-pin PQFP package.

## Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–21 through 4–24 describe the Cyclone device internal timing microparameters for LEs, IOEs, M4K memory structures, and MultiTrack interconnects.

**Table 4–21. LE Internal Timing Microparameter Descriptions**

Symbol	Parameter
$t_{SU}$	LE register setup time before clock
$t_H$	LE register hold time after clock
$t_{CO}$	LE register clock-to-output delay
$t_{LUT}$	LE combinatorial LUT delay for data-in to data-out
$t_{CLR}$	Minimum clear pulse width
$t_{PRE}$	Minimum preset pulse width
$t_{CLKHL}$	Minimum clock high or low time

Tables 4–34 through 4–35 show the external timing parameters on column and row pins for EP1C6 devices.

**Table 4–34. EP1C6 Column Pin Global Clock External I/O Timing Parameters**

Symbol	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSU}}$	2.691	—	3.094	—	3.496	—	ns
$t_{\text{INH}}$	0.000	—	0.000	—	0.000	—	ns
$t_{\text{OUTCO}}$	2.000	3.917	2.000	4.503	2.000	5.093	ns
$t_{\text{INSUPLL}}$	1.513	—	1.739	—	1.964	—	ns
$t_{\text{INHPLL}}$	0.000	—	0.000	—	0.000	—	ns
$t_{\text{OUTCOPLL}}$	0.500	2.038	0.500	2.343	0.500	2.651	ns

**Table 4–35. EP1C6 Row Pin Global Clock External I/O Timing Parameters**

Symbol	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSU}}$	2.774	—	3.190	—	3.605	—	ns
$t_{\text{INH}}$	0.000	—	0.000	—	0.000	—	ns
$t_{\text{OUTCO}}$	2.000	3.817	2.000	4.388	2.000	4.963	ns
$t_{\text{INSUPLL}}$	1.596	—	1.835	—	2.073	—	ns
$t_{\text{INHPLL}}$	0.000	—	0.000	—	0.000	—	ns
$t_{\text{OUTCOPLL}}$	0.500	1.938	0.500	2.228	0.500	2.521	ns

Tables 4–36 through 4–37 show the external timing parameters on column and row pins for EP1C12 devices.

**Table 4–36. EP1C12 Column Pin Global Clock External I/O Timing Parameters (Part 1 of 2)**

Symbol	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSU}}$	2.510	—	2.885	—	3.259	—	ns
$t_{\text{INH}}$	0.000	—	0.000	—	0.000	—	ns
$t_{\text{OUTCO}}$	2.000	3.798	2.000	4.367	2.000	4.940	ns
$t_{\text{INSUPLL}}$	1.588	—	1.824	—	2.061	—	ns

**Table 4–44. Cyclone I/O Standard Output Delay Adders for Slow Slew Rate on Column Pins (Part 2 of 2)**

I/O Standard		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	
1.5-V LVTTTL	2 mA	—	6,789	—	7,807	—	8,825	ps
	4 mA	—	5,109	—	5,875	—	6,641	ps
	8 mA	—	4,793	—	5,511	—	6,230	ps
SSTL-3 class I		—	1,390	—	1,598	—	1,807	ps
SSTL-3 class II		—	989	—	1,137	—	1,285	ps
SSTL-2 class I		—	1,965	—	2,259	—	2,554	ps
SSTL-2 class II		—	1,692	—	1,945	—	2,199	ps
LVDS		—	802	—	922	—	1,042	ps

**Table 4–45. Cyclone I/O Standard Output Delay Adders for Slow Slew Rate on Row Pins (Part 1 of 2)**

I/O Standard		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	
LVCMOS	2 mA	—	1,800	—	2,070	—	2,340	ps
	4 mA	—	1,311	—	1,507	—	1,704	ps
	8 mA	—	945	—	1,086	—	1,228	ps
	12 mA	—	807	—	928	—	1,049	ps
3.3-V LVTTTL	4 mA	—	1,831	—	2,105	—	2,380	ps
	8 mA	—	1,484	—	1,705	—	1,928	ps
	12 mA	—	973	—	1,118	—	1,264	ps
	16 mA	—	1,012	—	1,163	—	1,315	ps
	24 mA	—	838	—	963	—	1,089	ps
2.5-V LVTTTL	2 mA	—	2,747	—	3,158	—	3,570	ps
	8 mA	—	1,757	—	2,019	—	2,283	ps
	12 mA	—	1,763	—	2,026	—	2,291	ps
	16 mA	—	1,623	—	1,865	—	2,109	ps
1.8-V LVTTTL	2 mA	—	5,506	—	6,331	—	7,157	ps
	8 mA	—	4,220	—	4,852	—	5,485	ps
	12 mA	—	4,008	—	4,608	—	5,209	ps
1.5-V LVTTTL	2 mA	—	6,789	—	7,807	—	8,825	ps
	4 mA	—	5,109	—	5,875	—	6,641	ps
	8 mA	—	4,793	—	5,511	—	6,230	ps
3.3-V PCI		—	923	—	1,061	—	1,199	ps

**Table 4–47. Cyclone IOE Programmable Delays on Row Pins**

Parameter	Setting	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	
Decrease input delay to internal cells	Off	—	154	—	177	—	200	ps
	Small	—	2,212	—	2,543	—	2,875	ps
	Medium	—	2,639	—	3,034	—	3,430	ps
	Large	—	3,057	—	3,515	—	3,974	ps
	On	—	154	—	177	—	200	ps
Decrease input delay to input register	Off	—	0	—	0	—	0	ps
	On	—	3,057	—	3,515	—	3,974	ps
Increase delay to output pin	Off	—	0	—	0	—	0	ps
	On	—	556	—	639	—	722	ps

*Note to Table 4–47:*

- (1) EPC1C3 devices do not support the PCI I/O standard.

## Maximum Input and Output Clock Rates

Tables 4–48 and 4–49 show the maximum input clock rate for column and row pins in Cyclone devices.

**Table 4–48. Cyclone Maximum Input Clock Rate for Column Pins**

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTTL	464	428	387	MHz
2.5 V	392	302	207	MHz
1.8 V	387	311	252	MHz
1.5 V	387	320	243	MHz
LVC MOS	405	374	333	MHz
SSTL-3 class I	405	356	293	MHz
SSTL-3 class II	414	365	302	MHz
SSTL-2 class I	464	428	396	MHz
SSTL-2 class II	473	432	396	MHz
LVDS	567	549	531	MHz